



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SA2124 — PNP Epitaxial Planar Silicon Transistor High-Current Switching Applications

Applications

- Voltage regulators, relay drivers, lamp drivers, electrical equipment

Features

- Adoption of MBIT processes
- Low collector-to-emitter saturation voltage
- Large current capacity
- High-speed switching

Specifications

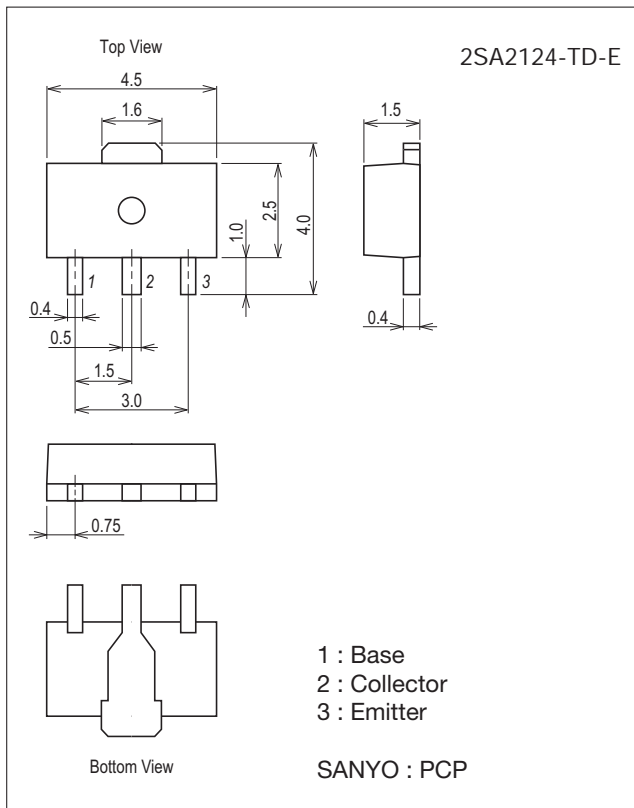
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-30	V
Collector-to-Emitter Voltage	VCEO		-30	V
Emitter-to-Base Voltage	VEBO		-6	V
Collector Current	IC		-2	A
Collector Current (Pulse)	ICP		-5	A

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Package Dimensions

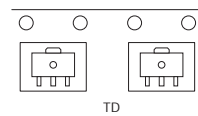
unit : mm (typ)
7007B-004



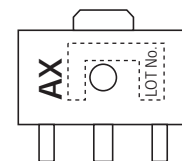
Product & Package Information

- Package : PCP
- JEITA, JEDEC : SC-62, SOT-89, TO-243
- Minimum Packing Quantity : 1,000 pcs./reel

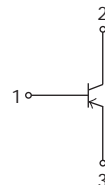
Packing Type: TD



Marking



Electrical Connection



2SA2124

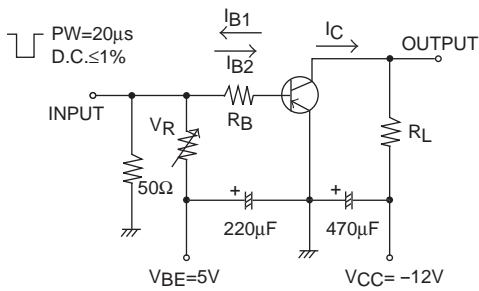
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Parameter	Symbol	Conditions	Ratings	Unit
Base Current	I_B		-400	mA
Collector Dissipation	P_C	When mounted on ceramic substrate (450mm ² ×0.8mm)	1.3	W
		$T_C=25^\circ\text{C}$	3.5	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0\text{A}$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0\text{A}$			-0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=-2\text{V}, I_C=-100\text{mA}$	200		560	
	h_{FE2}	$V_{CE}=-2\text{V}, I_C=-1.5\text{A}$	65			
Gain-Bandwidth Product	f_T	$V_{CE}=-10\text{V}, I_C=-300\text{mA}$		440		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.5\text{A}, I_B=-75\text{mA}$		-0.2	-0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-1.5\text{A}, I_B=-75\text{mA}$		-0.95	-1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0\text{A}$	-30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, R_{BE}=\infty$	-30			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0\text{A}$		-6		V
Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, f=1\text{MHz}$		17		pF
Turn-ON Time	t_{on}	See specified Test Circuit.		45		ns
Storage Time	t_{stg}			200		ns
Fall Time	t_f			23		ns

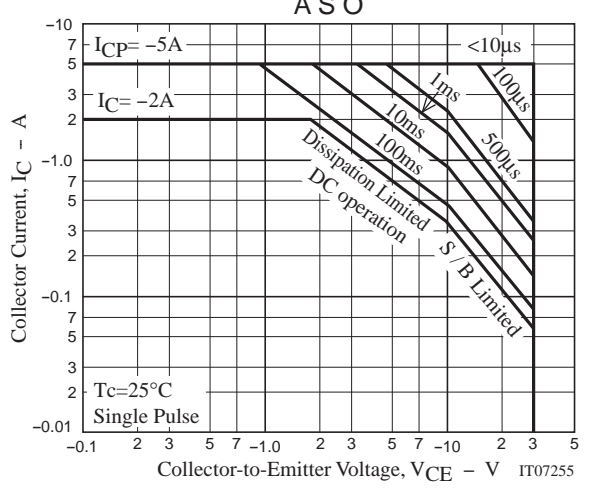
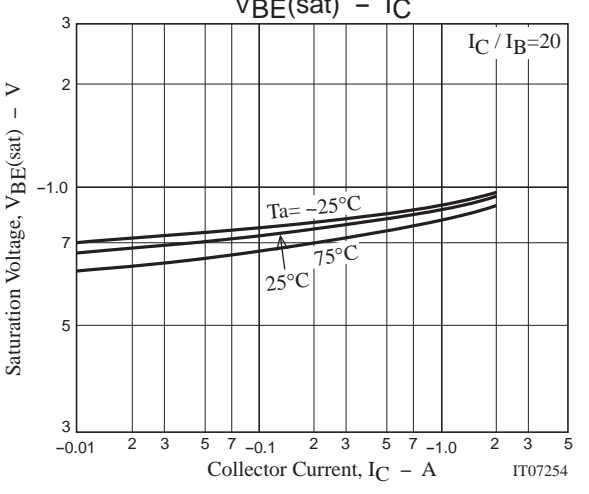
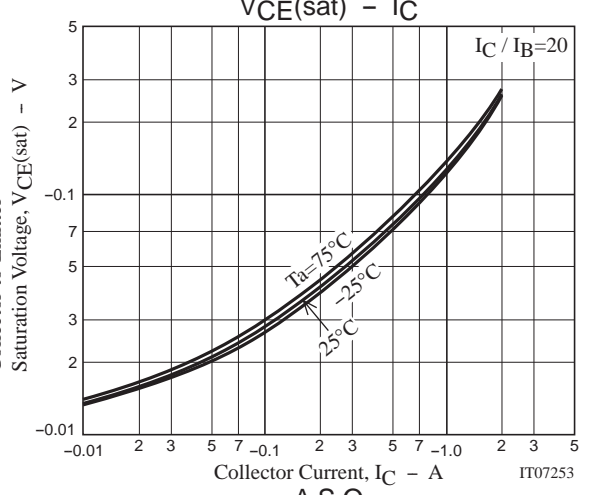
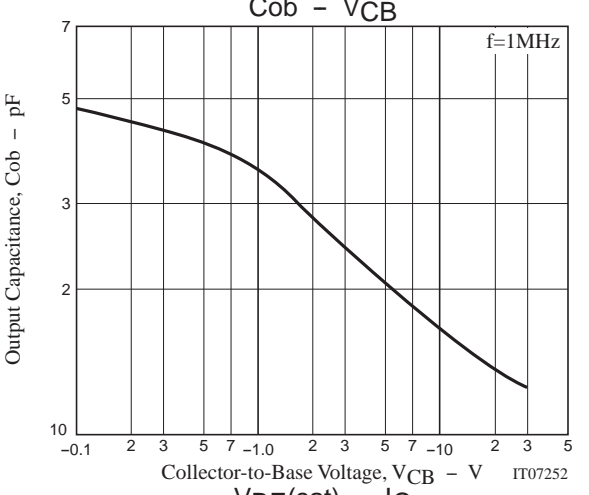
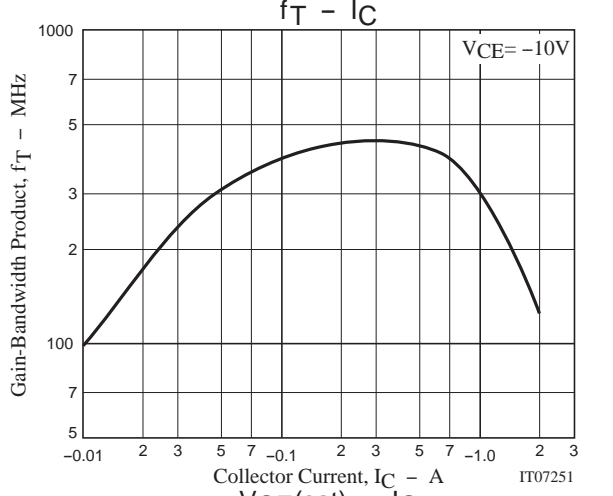
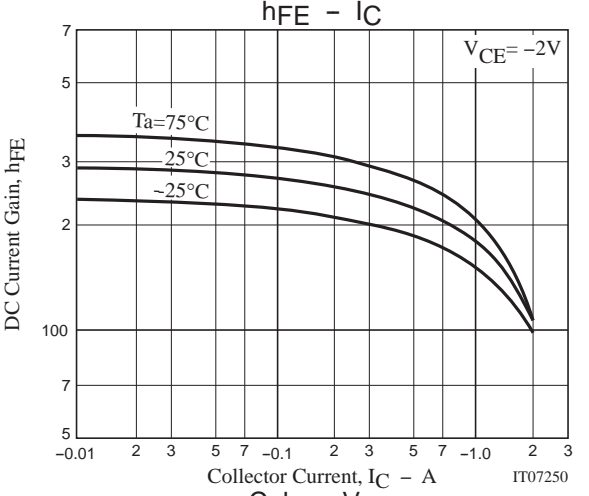
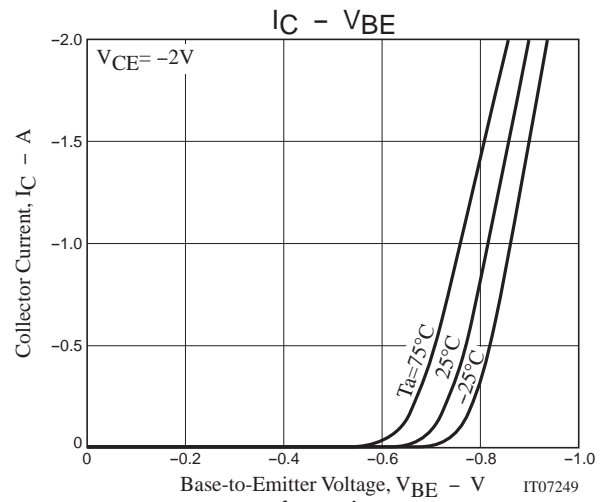
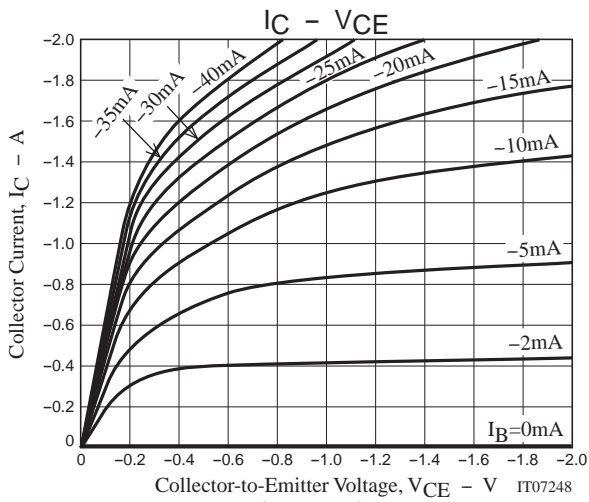
Switching Time Test Circuit



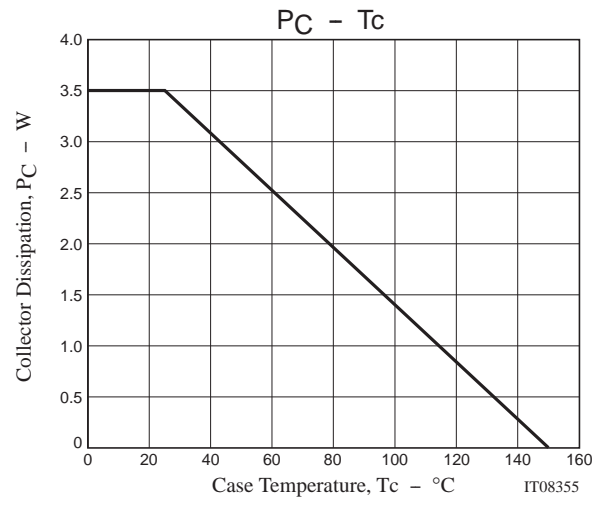
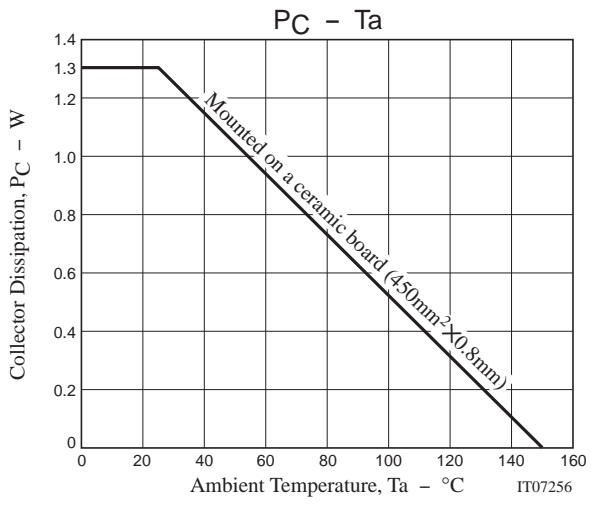
$$I_C = 20I_{B1} = -20I_{B2} = -0.5\text{A}$$

Ordering Information

Device	Package	Shipping	memo
2SA2124-TD-E	PCP	1,000pcs./reel	Pb Free



2SA2124



Bag Packing Specification

2SA2124-TD-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
PCP	PCP	1,000	4,000	24,000	4 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit :mm)

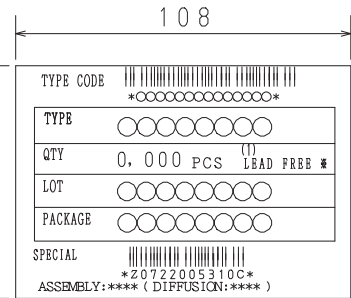
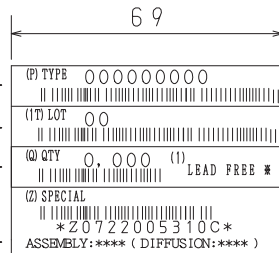
Outer box label
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Reel label

Type No.
LOT No.
Quantity
Origin



NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



Those with pin 1 index on the feed hole side.....TD

2SA2124

Outline Drawing

2SA2124-TD-E



Land Pattern Example



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